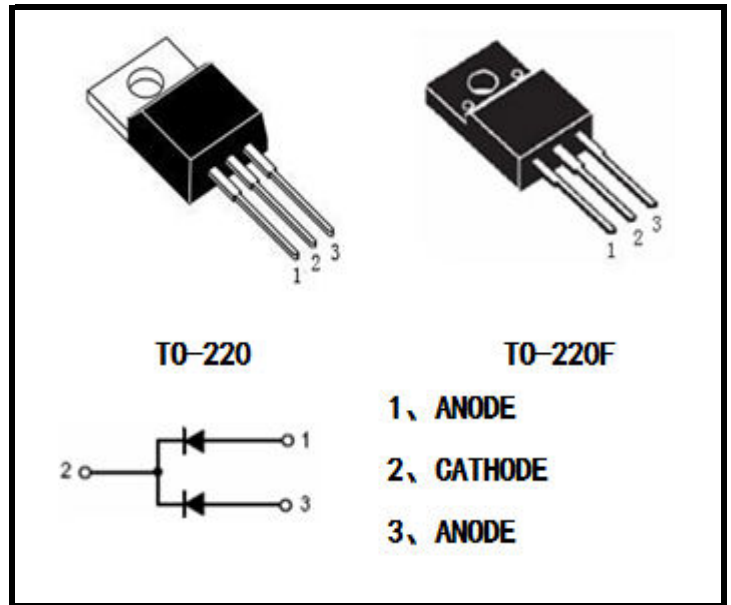


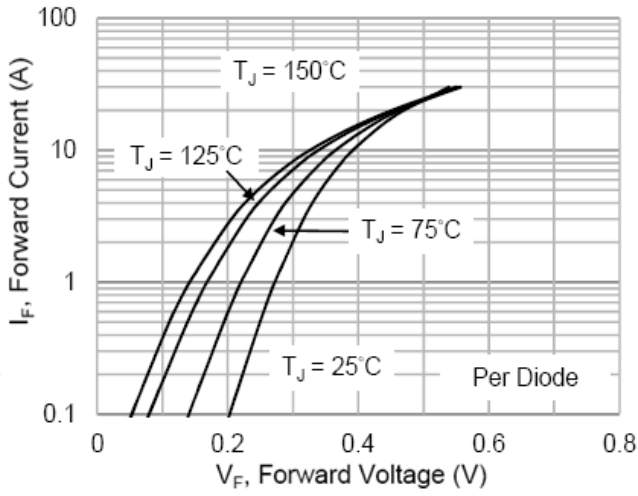
Ultra Low VF=0.28V at IF=5A
FEATURES

- * Schottky Barrier Chip
- * Guard Ring Die Construction for Transient Protection
- * Low Power Loss, High Efficiency
- * High Surge Capability
- * High Current Capability and Low Forward Voltage Drop
- * For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

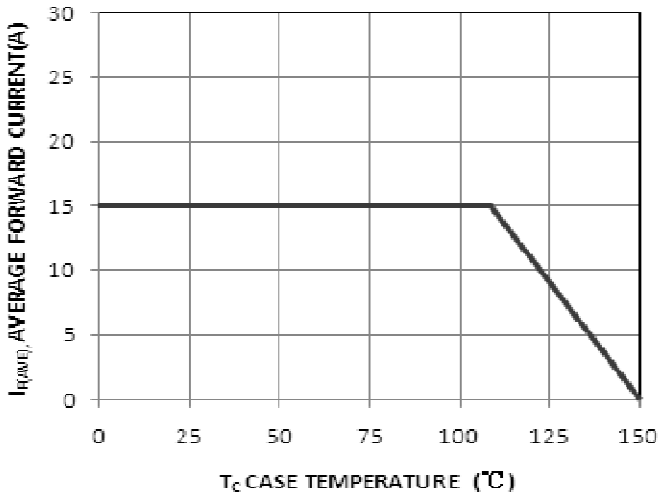
PACKAGE

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Characteristic	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage	V_{RRM}	45	V	
Working Peak Reverse Voltage	V_{RWM}			
DC Blocking Voltage	V_R			
Average Rectifide Output Current	$I_{F(per\ leg)}$	15	A	
	$I_{F(Total)}$	30		
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60Hz)	I_{FSM}	350	A	
Instaneous Forward Voltage @IF=5A, TC=25°C @IF=15A, TC=25°C @IF=5A, TC=125°C @IF=15A, TC=125°C	V_F	TYP.	V	
		0.36		
		0.46		
		0.28		
0.42				
Peak Reverse Current @Tc=25 °C at Rated DC Blocking Voltage @Tc=125°C	I_R	0.3 100	mA	
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C	
Maximum Thermal Resistance	θ_{JC}	TO-220	2	°C/W
		TO-220F	4	
	θ_{JA}	TO-220	60	
		TO-220F	60	

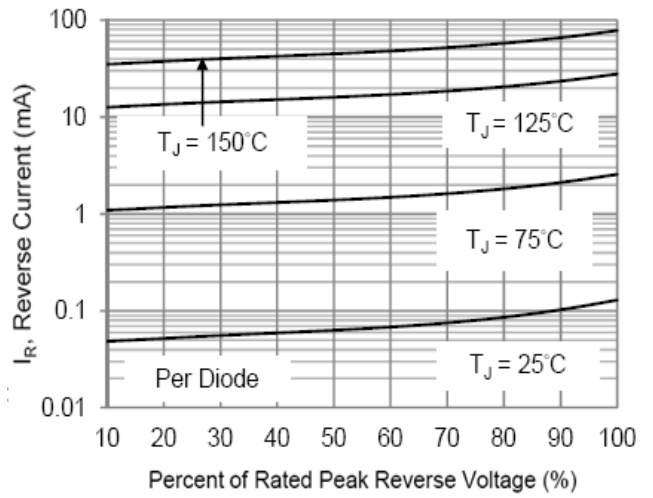
Characteristics Curves



Typical Forward Voltage Per Diode

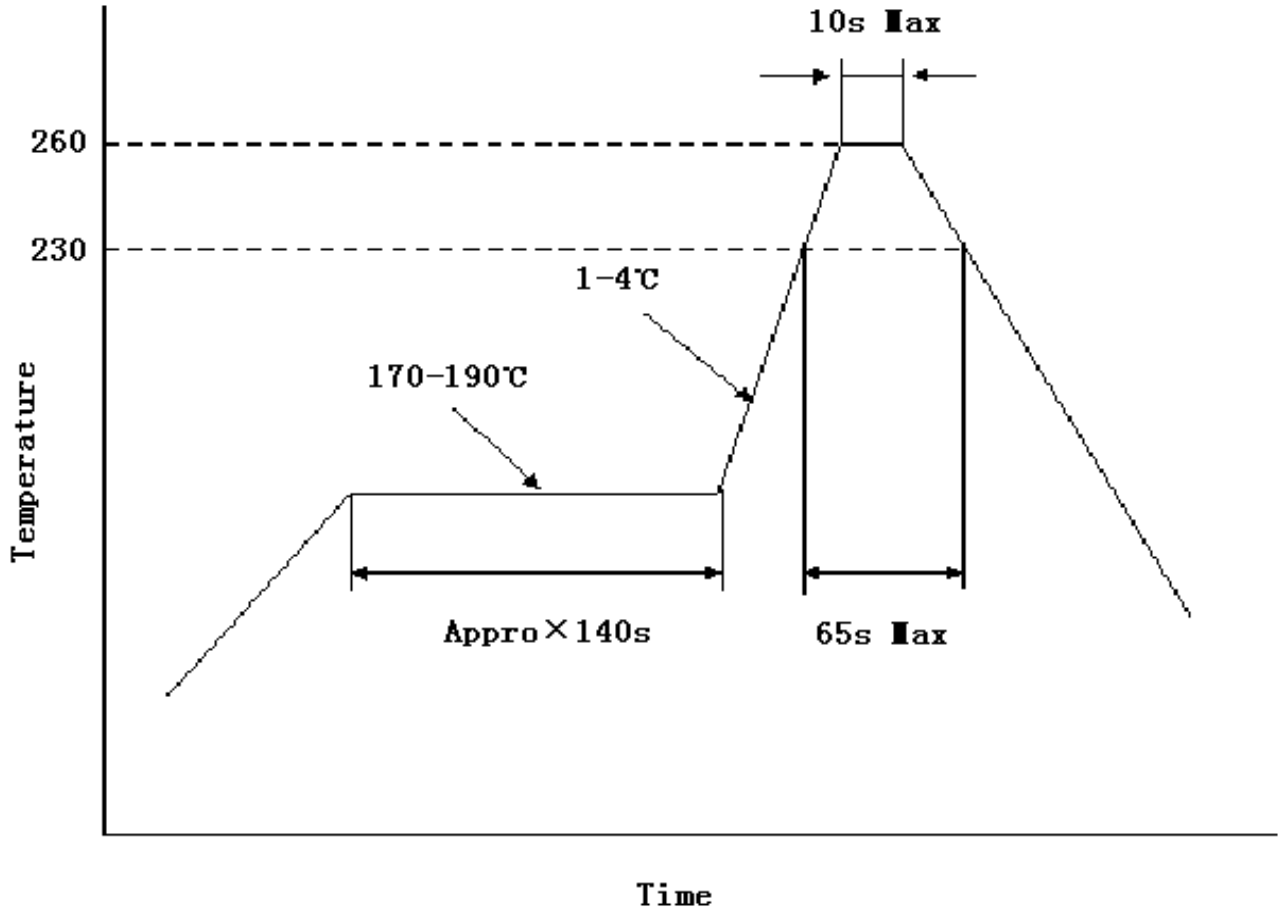


Average Forward Current vs. Case Temperature Per Diode



Typical Reverse Current Per Diode

■ Reflow Soldering Temperature Profile



T0-220 MECHANICAL DATA

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4		4.8	e	2.44	2.54	2.64
B	1.2		1.4	F	1.1		1.4
B1	1		1.4	L	12.5		14.5
b1	0.75		0.95	L1	3	3.5	4
c	0.4		0.55	ΦP	3.7	3.8	3.9
D	15		16.5	Q	2.5		3
D1	5.9		6.9	Q1	2		2.9
E	9.9		10.7				

